TOSHIBA Field Effect Transistor Silicon P-Channel MOS Type (π-MOS V)

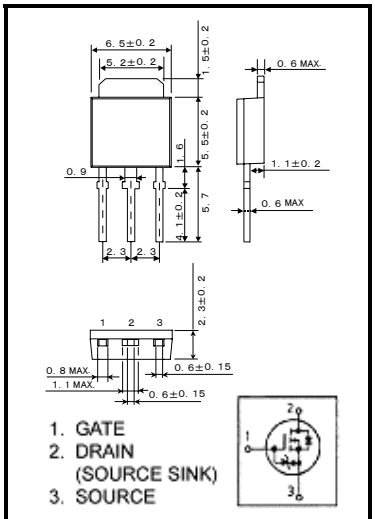
2SJ680

Switching Applications

Chopper Regulator, DC/DC Converter and Motor Drive Applications

- Low drain-source ON-resistance: $R_{DS\ (ON)}$ = 1.6 Ω (typ.)
- High forward transfer admittance: $|Y_{fs}|$ = 2.0 S (typ.)
- Low leakage current: I_{DSS} = −100 μA (max) (V_{DS} = −200 V)
- Enhancement model: V_{th} = −1.5 ~ −3.5 V (V_{DS} = −10 V, I_D = −1 mA)

Unit: mm



JEDEC	—
JEITA	—
TOSHIBA	2-7J2B

Weight: 0.36 g (typ.)

Maximum Ratings (Ta = 25°C)

Characteristic		Symbol	Rating	Unit
Drain-source voltage		V_{DSS}	−200	V
Drain-gate voltage (R_{GS} = 20 kΩ)		V_{DGR}	−200	V
Gate-source voltage		V_{GSS}	±20	V
Drain current	DC (Note 1)	I_D	−2.5	A
	Pulse (Note 1)	I_{DP}	−10	
Drain power dissipation (Tc = 25°C)		P_D	20	W
Single pulse avalanche energy (Note 2)		E_{AS}	97.5	mJ
Avalanche current		I_{AR}	−2.5	A
Repetitive avalanche energy (Note 3)		E_{AR}	2.0	mJ
Channel temperature		T_{ch}	150	°C
Storage temperature range		T_{stg}	−55~150	°C

Thermal Characteristics

Characteristic	Symbol	Max	Unit
Thermal resistance, channel to case	$R_{th\ (ch-c)}$	6.25	°C/W
Thermal resistance, channel to ambient	$R_{th\ (ch-a)}$	125	°C/W

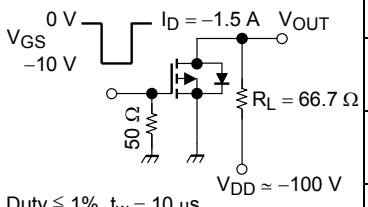
Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: V_{DD} = −50 V, Tch = 25°C (initial), L = −25.2 mH, I_{AR} = −2.5 A R_G = 25 Ω

Note 3: Repetitive rating: pulse width limited by maximum channel temperature

This transistor is an electrostatic-sensitive device. Handle with care.

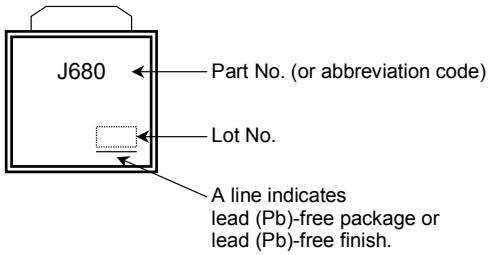
Electrical Characteristics (Ta = 25°C)

Characteristic		Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current		I_{GSS}	V_{GS} = ±16 V, V_{DS} = 0 V	—	—	±10	μA
Drain cutoff current		I_{DSS}	V_{DS} = −200 V, V_{GS} = 0 V	—	—	−100	μA
Drain-source breakdown voltage		$V_{(BR)\ DSS}$	I_D = −10 mA, V_{GS} = 0 V	−200	—	—	V
Gate threshold voltage		V_{th}	V_{DS} = −10 V, I_D = −1 mA	−1.5	—	−3.5	V
Drain-source ON-resistance		$R_{DS\ (ON)}$	V_{GS} = −10 V, I_D = −1.5 A	—	1.6	2.0	Ω
Forward transfer admittance		$\|Y_{fs}\|$	V_{DS} = −10 V, I_D = −1.5 A	1.0	2.0	—	S
Input capacitance		C_{iss}	V_{DS} = −10 V, V_{GS} = 0 V, f = 1 MHz	—	410	—	pF
Reverse transfer capacitance		C_{rss}		—	40	—	
Output capacitance		C_{oss}		—	145	—	
Switching time	Rise time	t_r		—	20	—	ns
	Turn-on time	t_{on}		—	45	—	
	Fall time	t_f		—	15	—	
	Turn-off time	t_{off}		—	85	—	
Total gate charge (gate-source plus gate-drain)		Q_g	V_{DD} ≃ −160 V, V_{GS} = −10 V, I_D = −2.5 A	—	10	—	nC
Gate-source charge		Q_{gs}		—	6	—	
Gate-drain (“Miller”) charge		Q_{gd}		—	4	—	

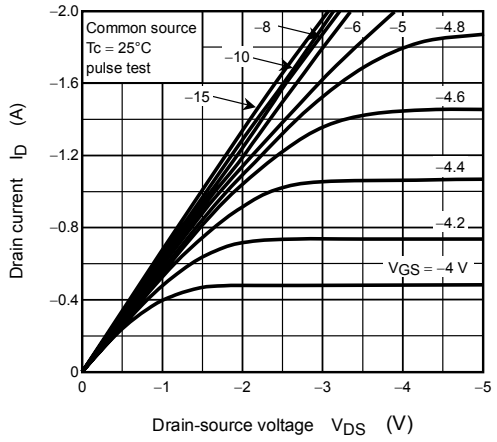
Source-Drain Ratings and Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Condition	Min	Typ.	Max	Unit
Continuous drain reverse current (Note 1)	I_{DR}	—	—	—	−2.5	A
Pulse drain reverse current (Note 1)	I_{DRP}	—	—	—	−10	A
Forward voltage (diode)	V_{DSF}	I_{DR} = −2.5 A, V_{GS} = 0 V	—	—	2.0	V
Reverse recovery time	t_{rr}	I_{DR} = −2.5 A, V_{GS} = 0 V, dI_{DR}/dt = 100 A/μs	—	135	—	ns
Reverse recovery charge	Q_{rr}		—	0.81	—	μC

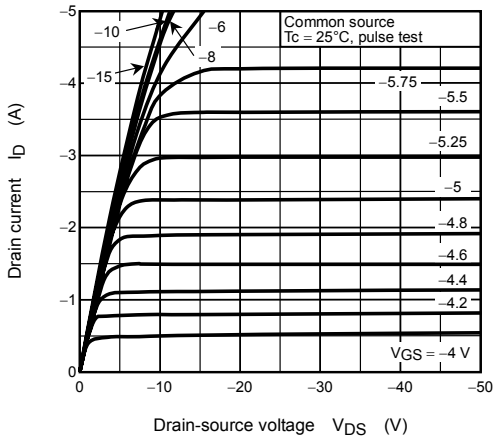
Marking



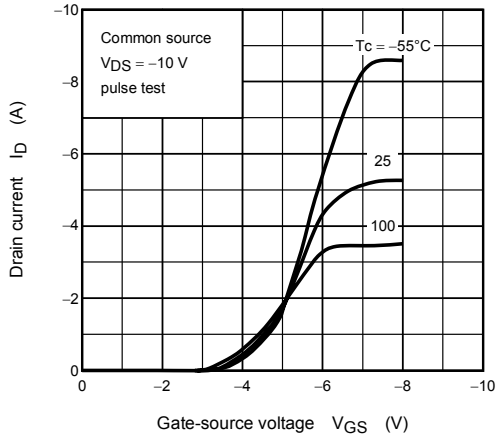
$I_D - V_{DS}$



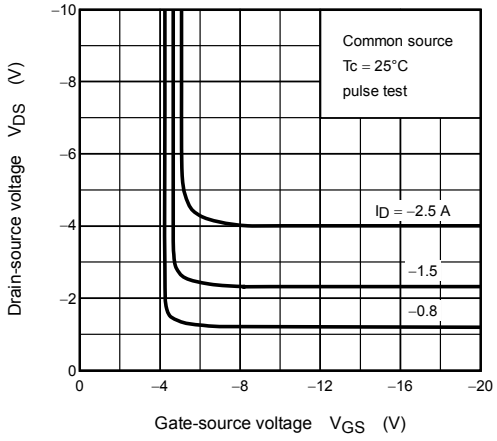
$I_D - V_{DS}$



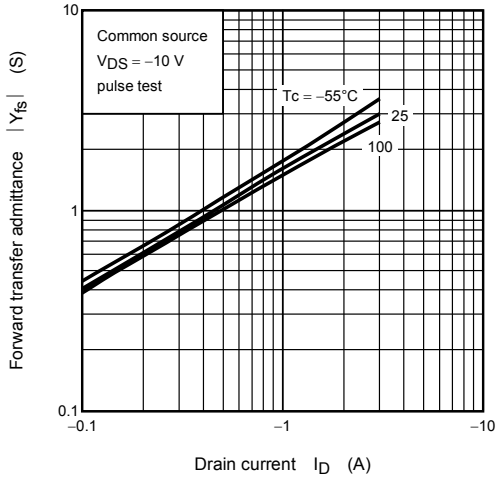
$I_D - V_{GS}$



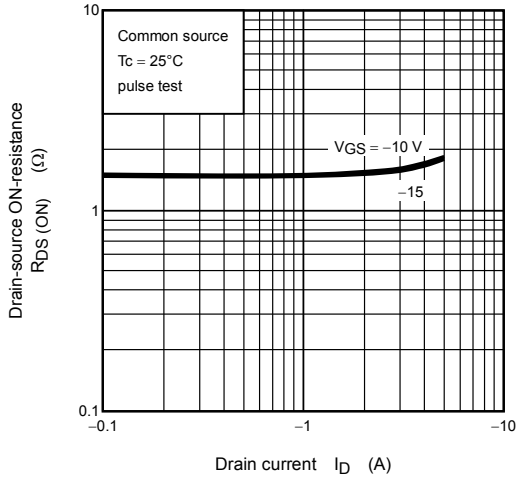
$V_{DS} - V_{GS}$



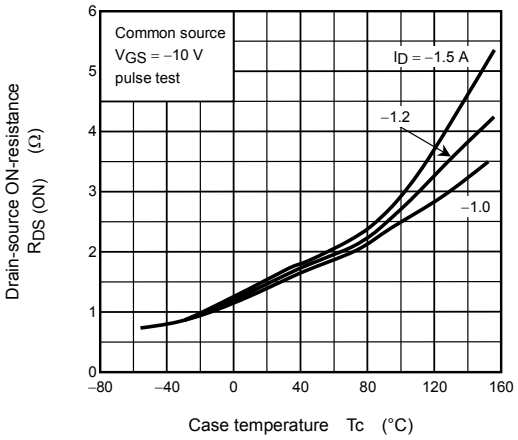
$|Y_{fs}| - I_D$



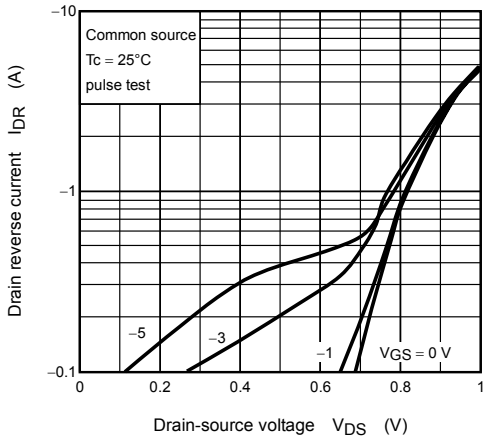
$R_{DS\ (ON)} - I_D$



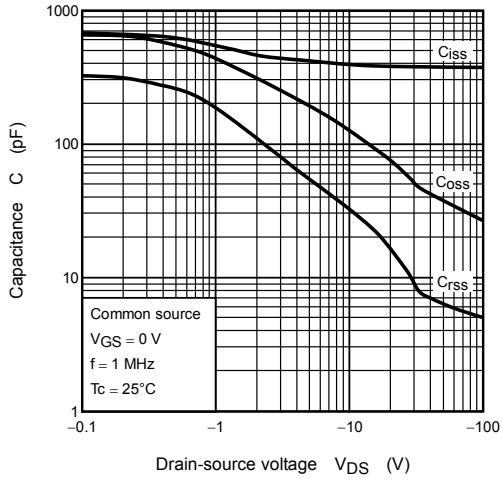
$R_{DS\ (ON)}$ – Tc



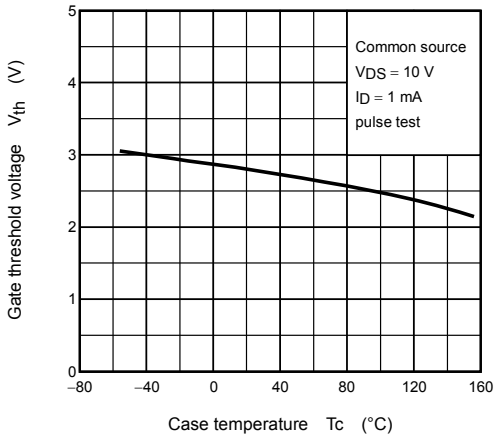
I_{DR} – V_{DS}



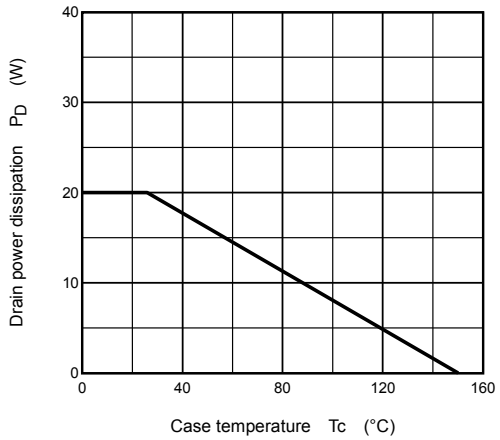
Capacitance – V_{DS}



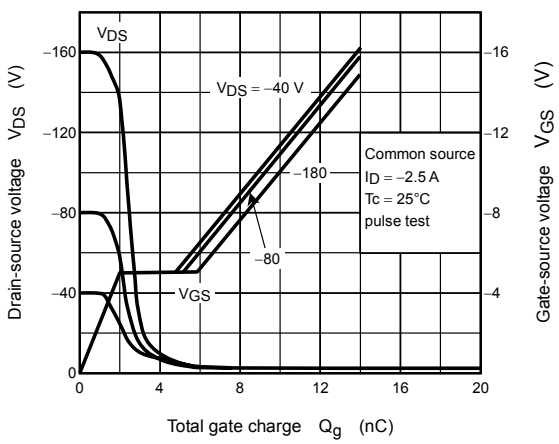
V_{th} – Tc



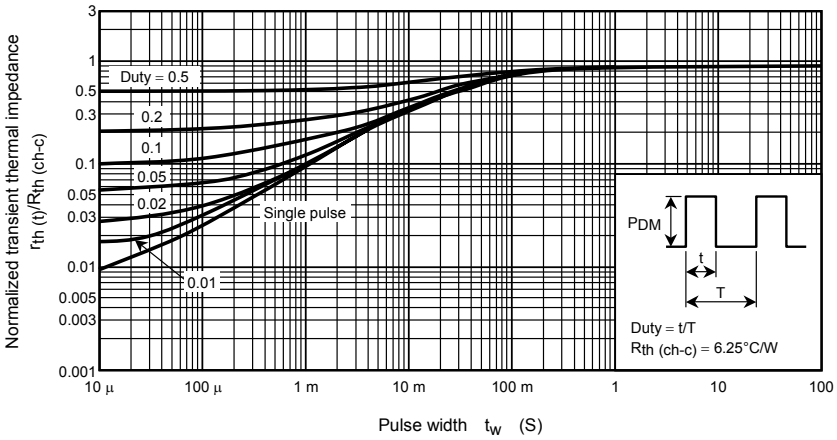
P_D – Tc



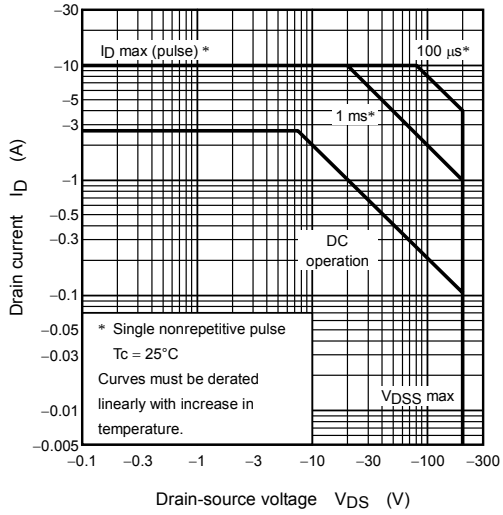
Dynamic input/output characteristics



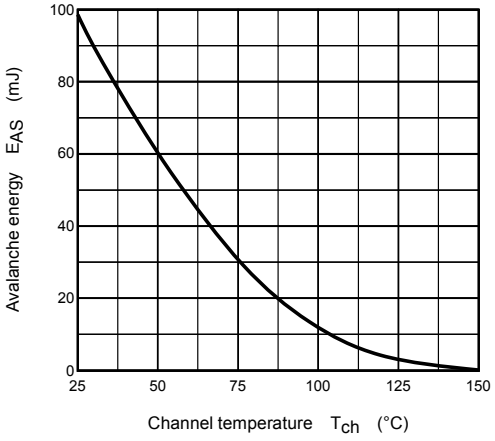
$r_{th} - t_w$

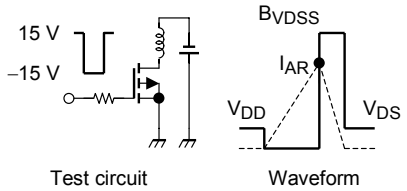


Safe operating area



$E_{AS} - T_{ch}$





Test circuit Waveform

$R_G = 25\ \Omega$
$V_{DD} = -50$ V, L = 25.2 mH

$$E_{AS} = \frac{1}{2} \cdot L \cdot I^2 \cdot \left(\frac{B_{VDSS}}{B_{VDSS} - V_{DD}} \right)$$

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